SPICE Model Parameters

Please copy this code from the SPICE model into LTSPICE (version 4) software for simulation of the GB10SLT12-CAL.

```
*      MODEL OF GeneSiC Semiconductor Inc.
*
*      $Revision:   1.0            $
*      $Date:   20-SEP-2013        $
*
*      GeneSiC Semiconductor Inc.
*      43670 Trade Center Place Ste. 155
*      Dulles, VA 20166
*
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*      ALL RIGHTS RESERVED
*
* These models are provided "AS IS, WHERE IS, AND WITH NO WARRANTY
* OF ANY KIND EITHER EXPRESSED OR IMPLIED, INCLUDING BUT NOT LIMITED
* TO ANY IMPLIED WARRANTIES OF MERCHANTABILITY AND FITNESS FOR A
* PARTICULAR PURPOSE."
* Models accurate up to 2 times rated drain current.
*
* Start of GB10SLT12-CAL SPICE Model
*
.SUBCKT GB10SLT12 ANODE KATHODE
D1 ANODE KATHODE GB10SLT12_SCHOTTKY
D2 ANODE KATHODE GB10SLT12_PIN
.MODEL GB10SLT12_SCHOTTKY D
+ IS      4.55E-15      RS      0.0736
+ N       1             IKF     1000
+ EG      1.2           XTI     -2
+ TRS1    0.0054347826  TRS2    2.71739E-05
+ CJO     6.40E-10      VJ      0.469
+ M       1.508         FC      0.5
+ TT      1.00E-10      BV      1200
+ IBV     1.00E-03      VPK     1200
+ IAVE    10            TYPE    SiC_Schottky
+ MFG     GeneSiC_Semi
.MODEL GB10SLT12_PIN D
+ IS      1.54E-22      RS      0.19
+ TRS1    -0.004        N       3.941
+ EG      3.23          IKF     19
+ XTI     0             FC      0.5
+ TT      0             BV      1200
+ IBV     1.00E-03      VPK     1200
+ IAVE    10            TYPE    SiC_PiN
.ENDS
*
* End of GB10SLT12-CAL SPICE Model
```